

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:)
Yuichiro Shindo) Examiner:
Application No.:) Group Art Unit:
Corresponding International Filing No.:)
PCT/JP2004/015777)
Filed: Herewith)
For: HIGH PURITY HAFNIUM,)
TARGET AND THIN FILM)
COMPRISING SAID HIGH)
PURITY HAFNIUM, AND)
METHOD FOR PRODUCING)
HIGH PURITY HAFNIUM)

Mail Stop PCT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

VERIFICATION OF TRANSLATION

Sir:

I, Isamu Ogoshi, having been warned that willful false statements and the like are punishable by fine or imprisonment or both, under section 1001 of Title 18 of the United States Code, and may jeopardize the validity of the above-captioned application and any patent issuing thereon, declare:

(1) I am a patent attorney authorized to practice law in Japan and am engaged in the practice of law with OGOSHI International Patent Office at Toranomon 9 Mori Bldg. 3F, 2-2, Atago 1-Chome, Minato-ku, Tokyo 105-0002, Japan.

(2) I am fluent in the Japanese and English Languages.

(3) I have reviewed the attached translation, and certify that it is an accurate English translation of the Japanese language international application of Yuichiro Shindo filed on October 25, 2004 and given International Application No. PCT/JP2004/015777.

(4) All of the statements made herein of my own knowledge are true and all statements made herein on information and belief are believed to be true.

April 27, 2006

Date

Isamu Ogoshi

Isamu Ogoshi